

Vishay Semiconductors

Silicon PIN Photodiode



DESCRIPTION

TEMD7100X01 is a high speed and high sensitive PIN photodiode. It is a miniature surface mount device (SMD) including the chip with a 0.23 mm² sensitive area and a daylight blocking filter matched with IR emitters operating at wavelength of 830 nm to 950 nm.

FEATURES

· Package type: surface mount

• Package form: 0805



• Radiant sensitive area (in mm²): 0.23

· AEC-Q101 qualified

· High radiant sensitivity

• Daylight blocking filter matched with 830 nm to AUTOMOTIVE 950 nm emitters



· Fast response times

• Angle of half sensitivity: $\varphi = \pm 60^{\circ}$

• Floor life: 168 h, MSL 3, acc. J-STD-020

· Lead (Pb)-free reflow soldering

• Compliant to RoHS directive 2002/95/EC and in accordance to WEEE 2002/96/EC

· Find out more about Vishay's Automotive Grade Product requirements at: www.vishay.com/applications

APPLICATIONS

- · High speed photo detector
- · Infrared remote control
- Infrared data transmission
- · Photo interrupters
- · Shaft encoders

PRODUCT SUMMARY				
COMPONENT	I _{ra} (μΑ)	φ (deg)	λ _{0.5} (nm)	
TEMD7100X01	3	± 60	750 to 1050	

Note

Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE PACKAGING		REMARKS	PACKAGE FORM		
TEMD7100X01	Tape and reel	MOQ: 3000 pcs, 3000 pcs/reel	0805		

Note

MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V_R	60	V	
Power dissipation	T _{amb} ≤ 25 °C	P _V	215	mW	
Junction temperature		T _j	100	°C	
Operating temperature range		T _{amb}	- 40 to + 100	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	Acc. reflow solder profile fig. 8	T _{sd}	260	°C	
Thermal resistance junction/ambient	Acc. J-STD-051	R _{thJA}	270	K/W	

T_{amb} = 25 °C, unless otherwise specified

Vishay Semiconductors

Silicon PIN Photodiode



BASIC CHARACTERISTICS						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
Forward voltage	I _F = 50 mA	V _F		1		V
Breakdown voltage	I _R = 100 μA, E = 0	V _(BR)	32			V
Reverse dark current	V _R = 10 V, E = 0	I _{ro}		1	10	nA
Diada sanasitanas	V _R = 0 V, f = 1 MHz, E = 0	C _D		4		pF
Diode capacitance	V _R = 5 V, f = 1 MHz, E = 0	C _D		1.3		pF
Open circuit voltage	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	Vo		350		mV
Temperature coefficient of V _o	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	TK _{Vo}		- 2.6		mV/K
Short circuit current	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	l _k		50		μΑ
Temperature coefficient of I _k	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}$	TK _{lk}		0.1		%/K
Reverse light current	$E_{e} = 1 \text{ mW/cm}^{2}, \lambda = 950 \text{ nm}, \ V_{R} = 5 \text{ V}$	I _{ra}		3		μΑ
Angle of half sensitivity		φ		± 60		deg
Wavelength of peak sensitivity		λ_{p}		950		nm
Range of spectral bandwidth		λ _{0.5}		750 to 1050		nm
Rise time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t _r		100		ns
Fall time	$V_R = 10 \text{ V}, R_L = 1 \text{ k}\Omega,$ $\lambda = 820 \text{ nm}$	t _f		100		ns

Note

 $T_{amb} = 25$ °C, unless otherwise specified

BASIC CHARACTERISTICS

 T_{amb} = 25 °C, unless otherwise specified

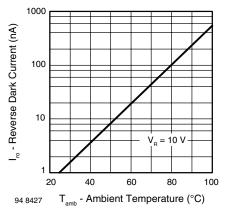


Fig. 1 - Reverse Dark Current vs. Ambient Temperature

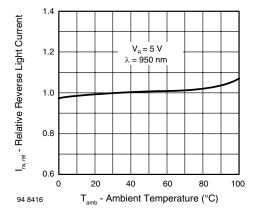


Fig. 2 - Relative Reverse Light Current vs. Ambient Temperature



Silicon PIN Photodiode

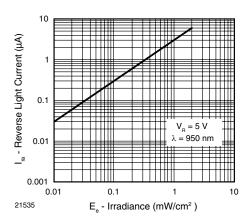


Fig. 3 - Reverse Light Current vs. Irradiance

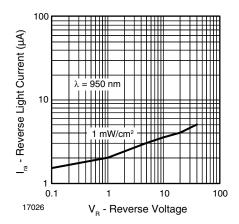


Fig. 4 - Reverse Light Current vs. Reverse Voltage

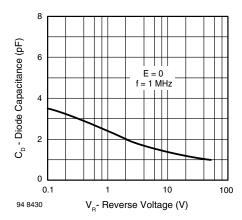


Fig. 5 - Diode Capacitance vs. Reverse Voltage

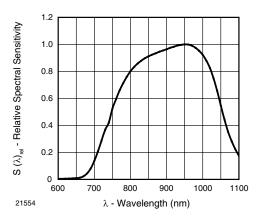


Fig. 6 - Relative Spectral Sensitivity vs. Wavelength

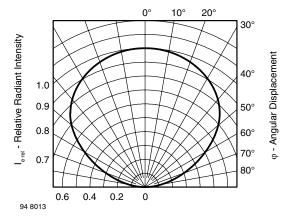


Fig. 7 - Relative Radiant Intensity vs. Angular Displacement

Vishay Semiconductors

Silicon PIN Photodiode



REFLOW SOLDER PROFILE

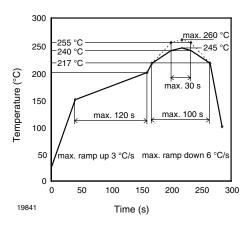


Fig. 8 - Lead (Pb)-free Reflow Solder Profile acc. J-STD-020D

DRYPACK

Devices are packed in moisture barrier bags (MBB) to prevent the products from moisture absorption during transportation and storage. Each bag contains a desiccant.

FLOOR LIFE

Floor life (time between soldering and removing from MBB) must not exceed the time indicated on MBB label:

Floor life: 168 h

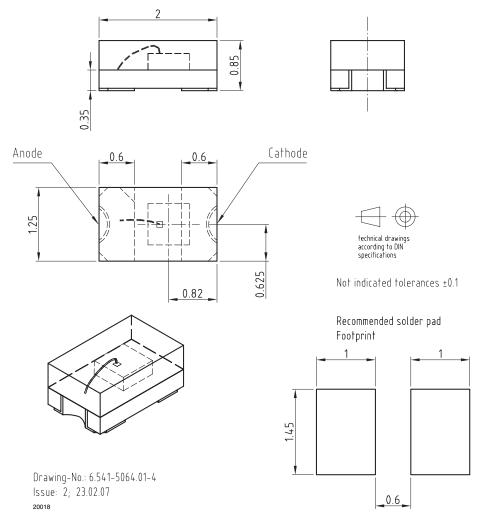
Conditions: T_{amb} < 30 °C, RH < 60 %

Moisture sensitivity level 3, acc. to J-STD-020.

DRYING

In case of moisture absorption devices should be baked before soldering. Conditions see J-STD-020 or label. Devices taped on reel dry using recommended conditions 192 h at 40 $^{\circ}$ C (+ 5 $^{\circ}$ C), RH < 5 $^{\circ}$ C.

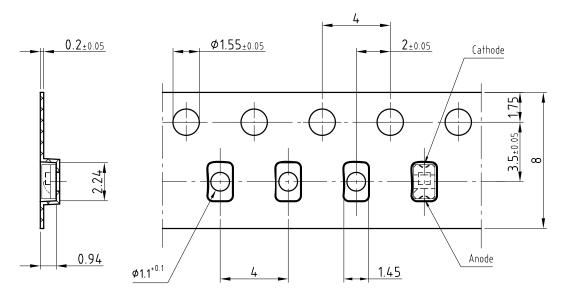
PACKAGE DIMENSIONS in millimeters



Silicon PIN Photodiode

Vishay Semiconductors

BLISTER TAPE DIMENSIONS in millimeters



Reel off direction

technical drawings according to DIN specifications

Drawing-No.: 9.700-5311.01-4

Issue: 1; 23.02.07

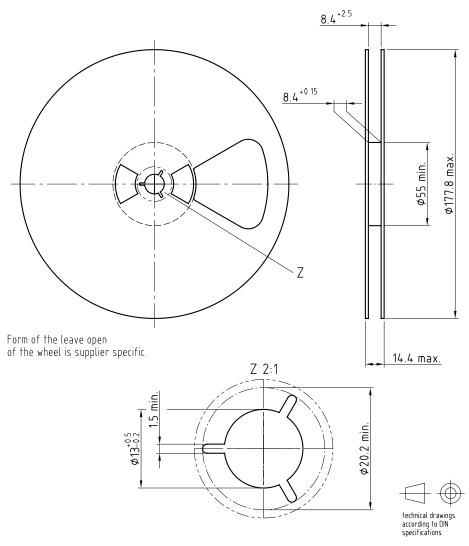
21501

Not indicated tolerances ±0.1

Silicon PIN Photodiode



REEL DIMENSIONS in millimeters



Drawing-No.: 9.800-5096.01-4

Issue: 1; 05.05.08

20875



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.